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APPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/988,183	11/19/2001	Kilho Lee	2001 P 11904 US 8136		
7590 12/30/2003			EXAMINER		
Law Office of Jerome J. Norris			HA, NATHAN W		
Suite 305 1901 Pennsylvania Avenue, N.W.			ART UNIT	PAPER NUMBER	
Washington, DC 20006			2814	, /	
		•	DATE MAILED: 12/30/2003	7	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application	on No. Applicant(s)						
Office Action Summary		09/988,18	33	LEE ET AL.					
		Examiner	•	Art Unit					
		Nathan W		2814	AW				
Period fo	The MAILING DATE of this communication a or Reply	appears on the	e cover sheet with the c	orrespondence ac	ldress				
THE I - Exter after - If the - If NC - Failu - Any	ORTENED STATUTORY PERIOD FOR REF MAILING DATE OF THIS COMMUNICATION mailed by available under the provisions of 37 CFR SIX (6) MONTHS from the mailing date of this communication. It period for reply specified above is less than thirty (30) days, a soperiod for reply is specified above, the maximum statutory perior to reply within the set or extended period for reply will, by state to receive the original process of the maximum statutory perior to reply within the set or extended period for reply will, by state to receive the original process of the maximum statutory perior to reply within the set or extended period for reply will, by state places are processed by the Office later than three months after the maximum adjustment. See 37 CFR 1.704(b).	N. 1.136(a). In no every reply within the state od will apply and we tute, cause the app	ent, however, may a reply be timutory minimum of thirty (30) daysill expire SIX (6) MONTHS from lication to become ABANDONE	nely filed s will be considered time the mailing date of this o D (35 U.S.C. § 133).					
1)⊠	Responsive to communication(s) filed on 30	November 2	<u>001</u> .						
2a) <u></u> ☐	☐ This action is FINAL . 2b) ☐ This action is non-final.								
3)□	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.								
Dispositi	ion of Claims								
5)□ 6)⊠ 7)⊠	 ✓ Claim(s) 1-10 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. ☐ Claim(s) is/are allowed. ✓ Claim(s) 1-3 and 7-10 is/are rejected. ✓ Claim(s) 4-6 is/are objected to. ☐ Claim(s) are subject to restriction and/or election requirement. 								
•	ion Papers								
10)	The specification is objected to by the Exam The drawing(s) filed on is/are: a) a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correction of the oath or declaration is objected to by the	accepted or b) the drawing(s) b rection is requir	ne held in abeyance. See red if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 C					
	under 35 U.S.C. §§ 119 and 120								
12)									
2) Notic	nt(s) De of References Cited (PTO-892) De of Draftsperson's Patent Drawing Review (PTO-948) The mation Disclosure Statement(s) (PTO-1449) Paper No((PTO-413) Paper No Patent Application (PT					

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Art Unit: 2814

DETAILED ACTION

It is noted that that prior art mentioned in the specification have been considered, US 6,159,810, 5,278,096, and 5,464,789. However, there was no IDS form (PTO-1449) enclosed in the file.

Specification

1. Applicant is reminded of the proper language and format for an abstract of the disclosure.

The abstract should be in narrative form and generally limited to a single paragraph on a separate sheet within the range of 50 to 150 words. It is important that the abstract not exceed 150 words in length since the space provided for the abstract on the computer tape used by the printer is limited. The form and legal phraseology often used in patent claims, such as "means" and "said," should be avoided. The abstract should describe the disclosure sufficiently to assist readers in deciding whether there is a need for consulting the full patent text for details.

The language should be clear and concise and should not repeat information given in the title. It should avoid using phrases which can be implied, such as, "The disclosure concerns," "The disclosure defined by this invention," "The disclosure describes," etc.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.
- 3. Claims 1-3 and 7-10 are rejected under 35 U.S.C. 102(a) as being anticipated by Yang, US 6,159,810.

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In regard to claim 1, in figs 4-12, Yang discloses a method of making a dual work function gate electrode of a CMOS semiconductor structure, the improvement comprising formation of the dual work function gate electrode comprising:

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- a) forming a gate oxide layer 23 over a channel of a nMOS site and over a channel of a pMOS site;
- b) forming an undoped polysilicon layer 33 over said gate oxide layer;
- c) masking said pMOS site, forming an a-Si layer over said nMOS site using a first heavy ion implantation, and implanting arsenic solely into said a- Si layer;
- d) masking said nMOS site formed by step c), forming an a-Si layer over said pMOS site using a second heavy ion implantation, and implanting boron solely into said a -Si regions;
- e) laser annealing said nMOS and pMOS sites for a sufficient period of time and at an energy level sufficient to melt at least a portion of the a- Si but insufficient to melt the polysilicon; and
- f) affecting cooling after laser annealing to convert a- Si into polysilicon without gate oxide damage; see also cols. 4-5.

In regard to claims 2-3 and 7-10, the method of claim 1 wherein in step c), said first

heavy ion implantation is affected by selecting a material from the group consisting of Ge or Si; see col. 4, lines 47-52. Art Unit: 2814

Allowable Subject Matter

4. Claims 4-6 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Nathan W. Ha whose telephone number is (703) 305-3507. The examiner can normally be reached on M-TH 8:00-7:00(EST).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (703) 308-4918. The fax phone number for the organization where this application or proceeding is assigned is (703) 308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Nathan Ha

December 27, 2003

PHIMARY EXAMINE